

General Description

This MOSFET uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.

Features

- Low gate charge
- 100% UIS tested, 100% DVDS tested
- High power and current handling capability
- Lead free product is acquired

Applications

- Load switch
- DC/DC converter for LCD display



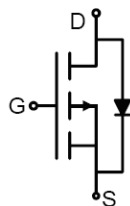
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(ON), max} @ V_{GS}=-10V$	9.4	m Ω

Marking Information

Product Name	Package	Marking
OSH06P09GF	PDFN5X6-8L	OSH06P09G

Package & Pin information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	-60	V
Gate-source voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-86	A
Pulsed Drain Current ¹⁾	$I_{D,pulse}$	-344	A
Power Dissipation	P_D	120	W
Single pulsed avalanche energy ²⁾	E_{AS}	650	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	1.04	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	-60			V	$V_{GS}=0\text{ V}, I_D=-250\ \mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	-1.0		-2.5	V	$V_{DS}=V_{GS}, I_D=-250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(ON)}$		7.2	9.4	$\text{m}\Omega$	$V_{GS}=-10\text{ V}, I_D=-20\text{ A}$
Drain-source on-state resistance	$R_{DS(ON)}$		8.6	11.4	$\text{m}\Omega$	$V_{GS}=-4.5\text{ V}, I_D=-20\text{ A}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$
				-100		$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$
Drain-source leakage current	I_{DSS}			-1	μA	$V_{DS}=-60\text{ V}, V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		13336		pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1.0\text{ MHz}$
Output capacitance	C_{oss}		510		pF	
Reverse transfer capacitance	C_{rss}		471		pF	
Gate resistance	R_g		1.7		Ω	$V_{GS}=0\text{ V}$, $V_{DS}=0\text{ V}$, $f=1.0\text{ MHz}$
Turn-on Delay Time	$t_{d(on)}$		26		ns	$V_{GS}=-10\text{ V}$, $V_{DS}=-30\text{ V}$, $R_L=1.5\ \Omega$, $R_{GEN}=3\ \Omega$
Turn-on Rise Time	t_r		33		ns	
Turn-Off Delay Time	$t_{d(off)}$		274		ns	
Turn-Off Fall Time	t_f		90		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total Gate Charge	Q_g		197		nC	$V_{GS}=-10\text{ V}$, $V_{DS}=-30\text{ V}$, $I_D=-20\text{ A}$
Gate-Source Charge	Q_{gs}		26		nC	
Gate-Drain Charge	Q_{gd}		45		nC	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Source drain current (Body Diode)	I_{SD}			-86	A	$T_A=25^\circ\text{C}$
Diode forward voltage ³⁾	V_{SD}			-1.2	V	$I_S=-20\text{ A}$, $V_{GS}=0\text{ V}$
Reverse Recovery Time	t_{rr}		36.4		ns	$I_F=-20\text{ A}$, $di/dt=100\text{ A/us}$
Reverse Recovery Charge	Q_{rr}		43.7		nC	

- Note:**
- 1) Pulse width limited by maximum allowable junction temperature.
 - 2) EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=-40\text{V}$, $V_G=-10\text{V}$, $R_g=25\ \Omega$, $L=0.5\text{mH}$.
 - 3) Repetitive Rating: Pulse width limited by maximum junction temperature.

Electrical Characteristics Diagrams

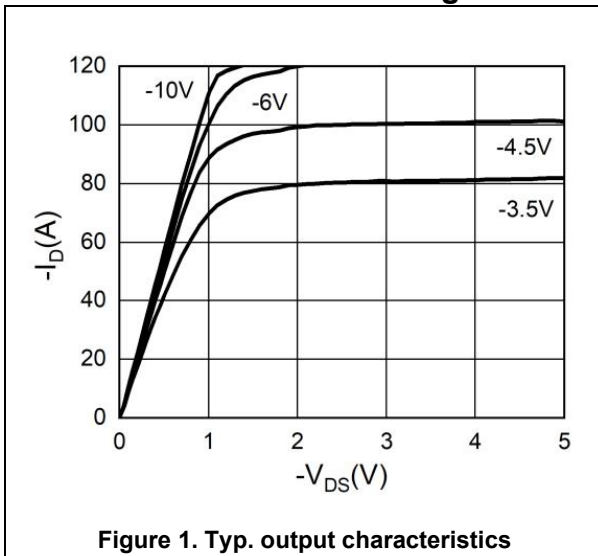


Figure 1. Typ. output characteristics

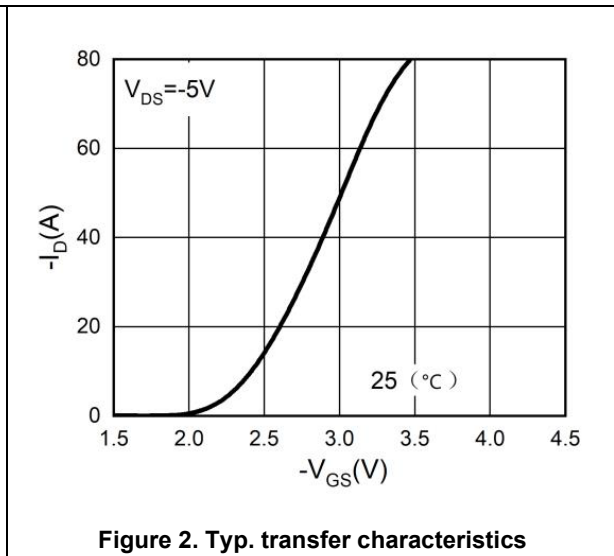


Figure 2. Typ. transfer characteristics

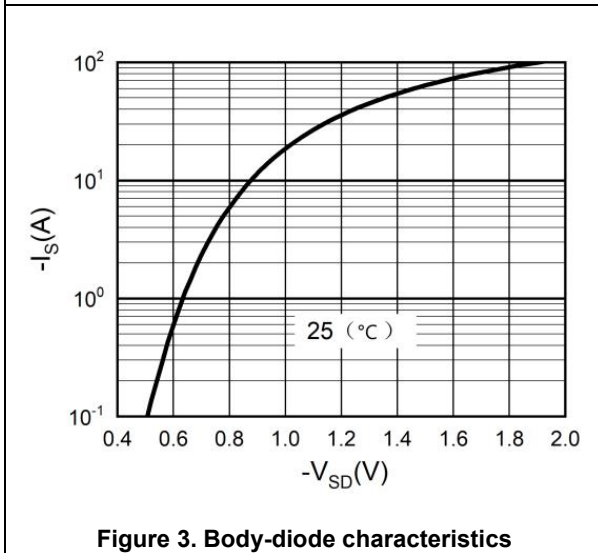


Figure 3. Body-diode characteristics

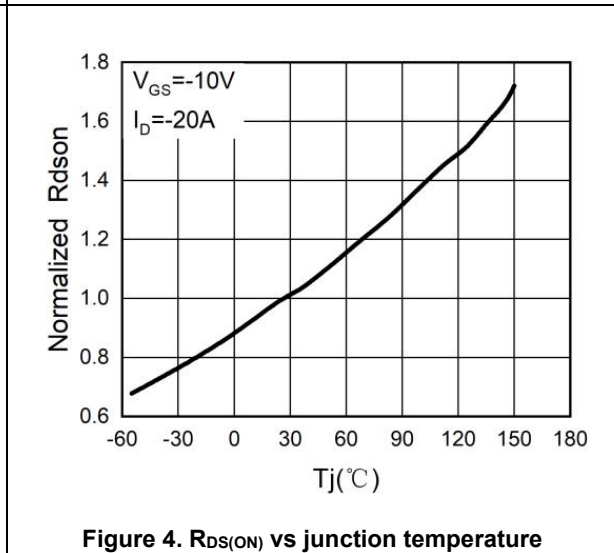


Figure 4. R_DS(ON) vs junction temperature

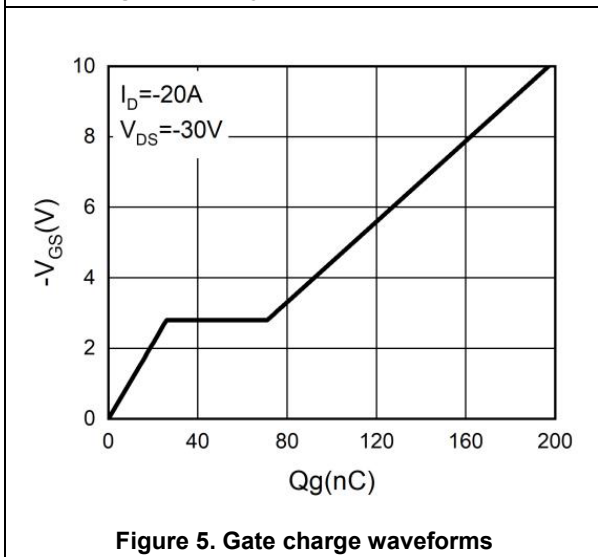


Figure 5. Gate charge waveforms

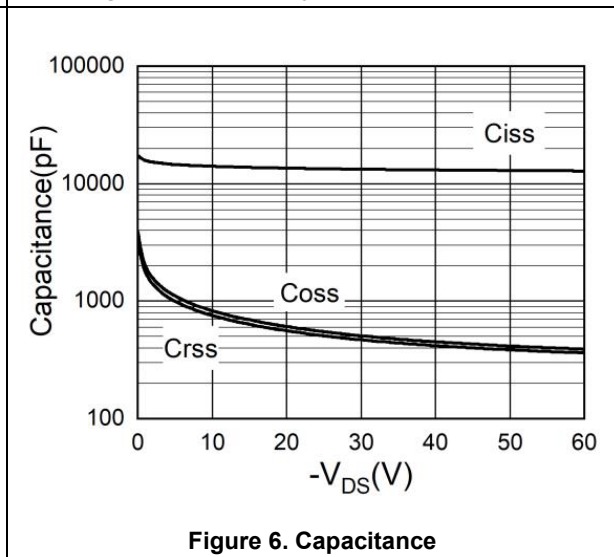
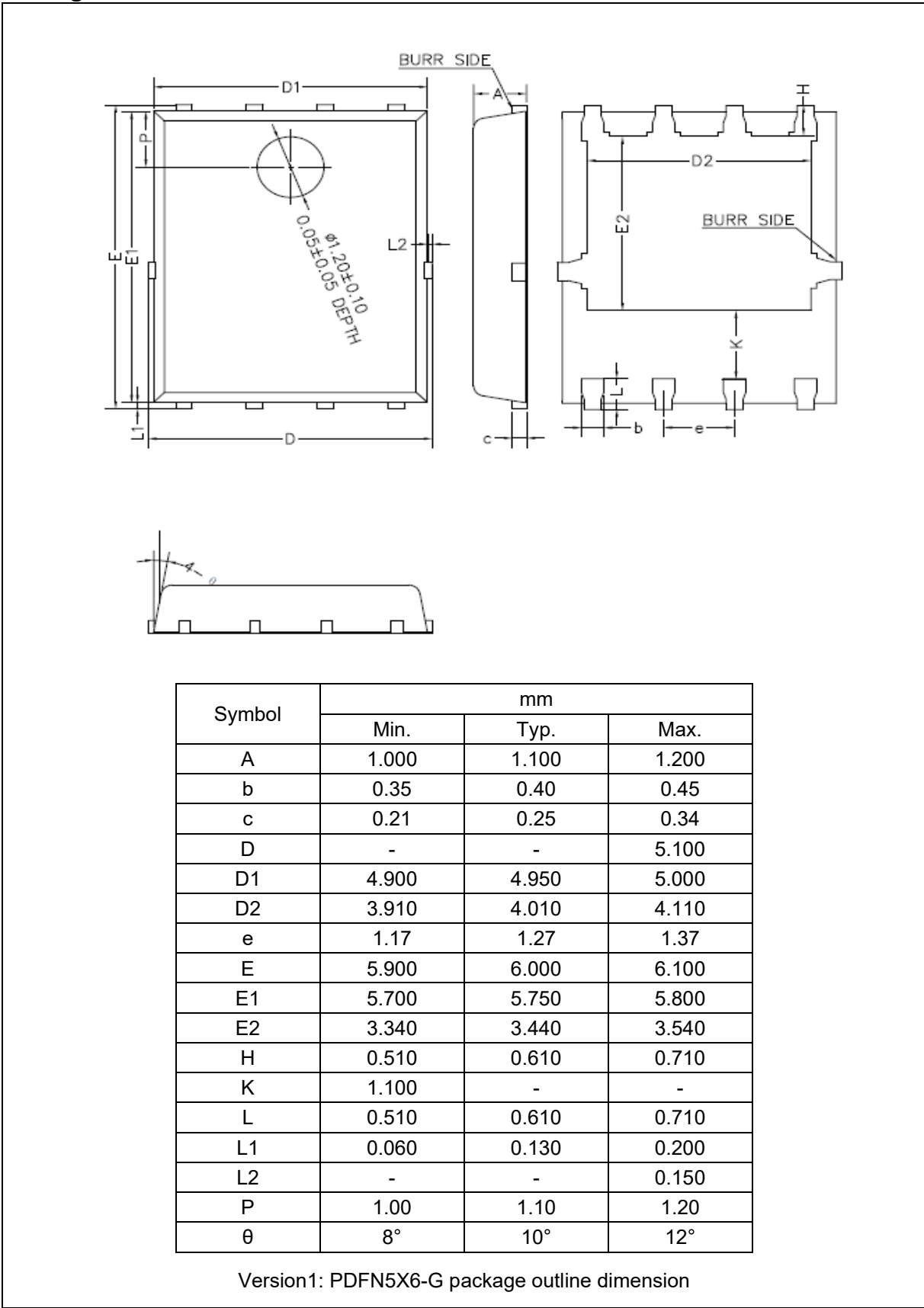


Figure 6. Capacitance

Package Information



Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
PDFN5X6-G	5000	2	10000	6	60000

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